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| INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) | Atty. Docket No. | Serial No. |
| | 160-386 | 10/609,410 |
| | Applicant | |
| | NAKAMURA et al. | |
| | Filing Date | TC/A.U. |
| | JULY 1, 2003 | 2825 |

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TRANSLATION

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N-Yasharov

Date Considered

08/10/05

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07/01/03

10/609,410

| INFORMATION DISCLOSURE CITATION | | ATTY. DOCKET NO. <u>160-386</u> | DIVISIONAL OF SERIAL NO. <u>10/292,583</u> | | | |
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| | | APPLICANT <u>NAKAMURA et al</u> | | | | |
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***Examiner**

V. Yegorov

Date Considered

~~04/26/05~~

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*Examiner V. Yeshtov Date Considered 09/26/05

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